

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

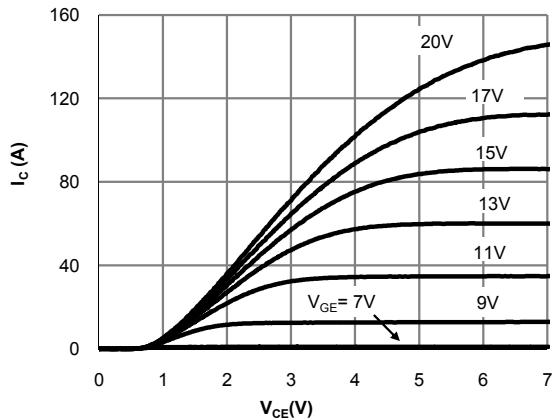


Fig 1: Output Characteristic
($T_j=25^\circ\text{C}$)

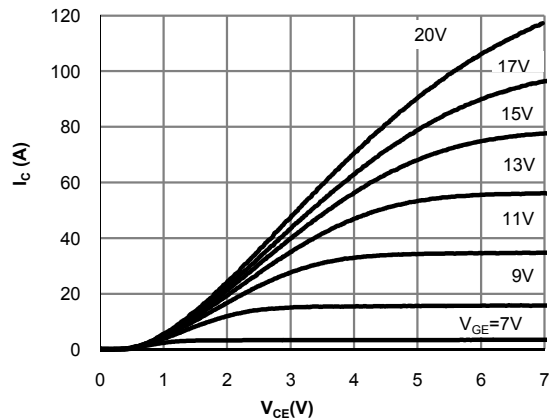


Fig 2: Output Characteristic
($T_j=150^\circ\text{C}$)

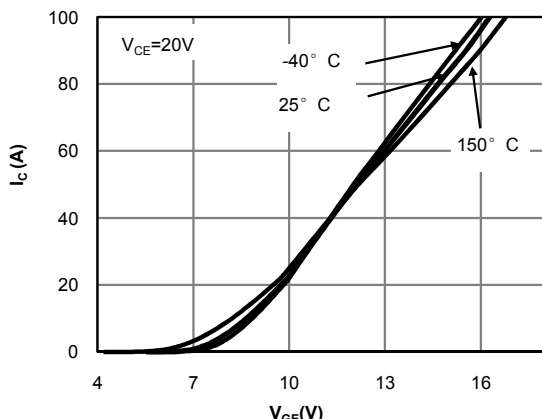


Fig 3: Transfer Characteristic

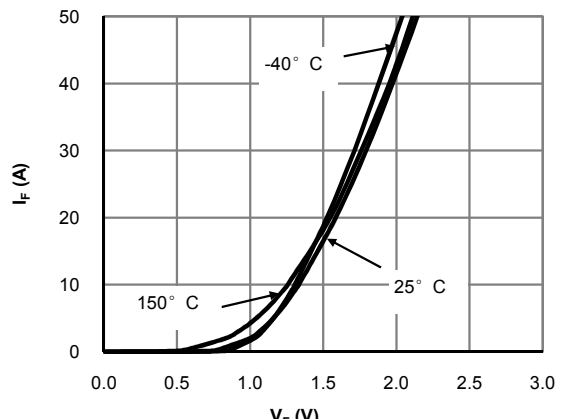


Fig 4: Diode Characteristic

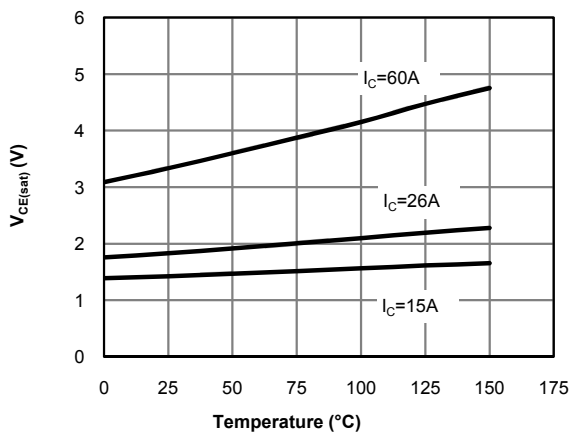


Fig 5: Collector-Emitter Saturation Voltage vs. Junction Temperature

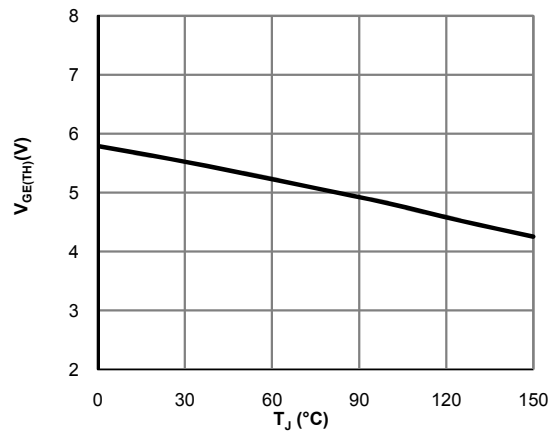


Figure 6: $V_{GE(TH)}$ vs. T_j

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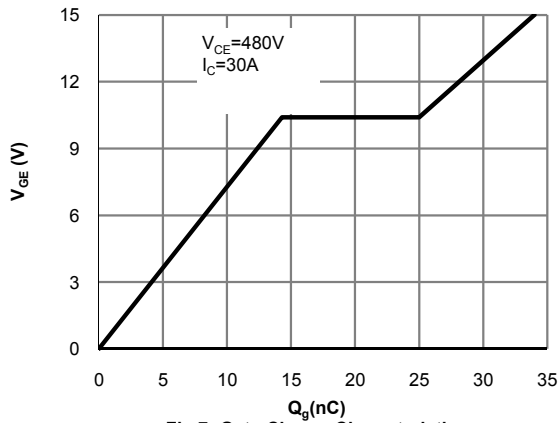


Fig 7: Gate-Charge Characteristics

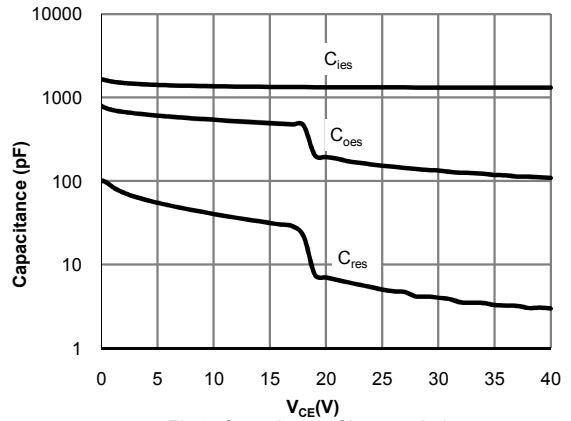


Fig 8: Capacitance Characteristic

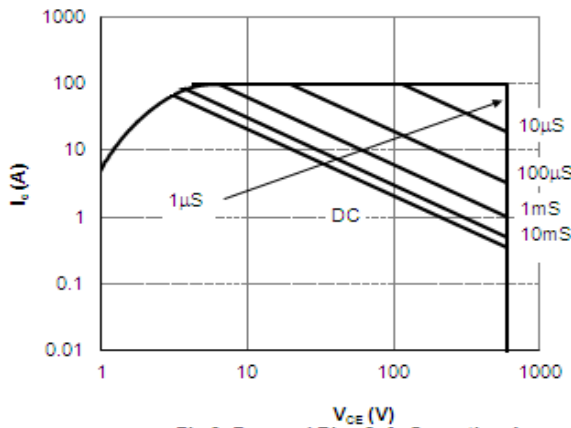


Fig 9: Forward Bias Safe Operating Area
($T_c=25^\circ\text{C}, V_{GE}=15\text{V}$)

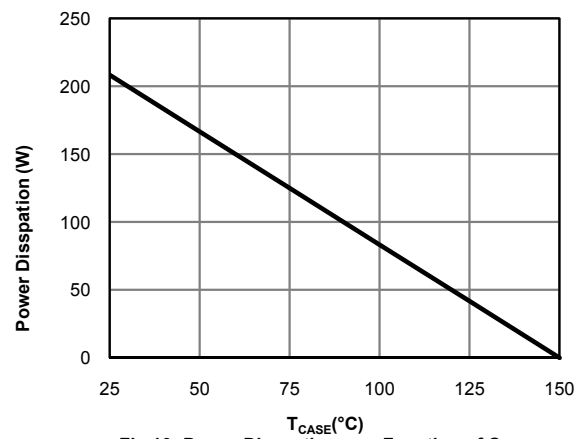


Fig 10: Power Dissipation as a Function of Case

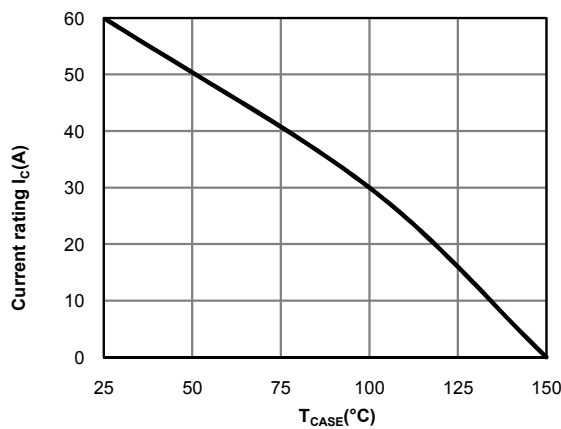


Fig 11: Current De-rating

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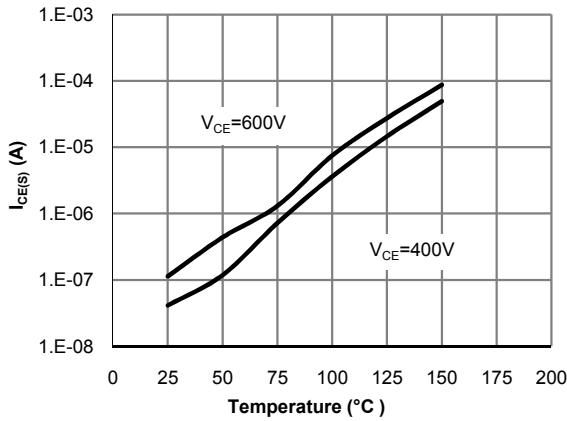


Fig 19: Diode Reverse Leakage Current vs. Junction Temperature

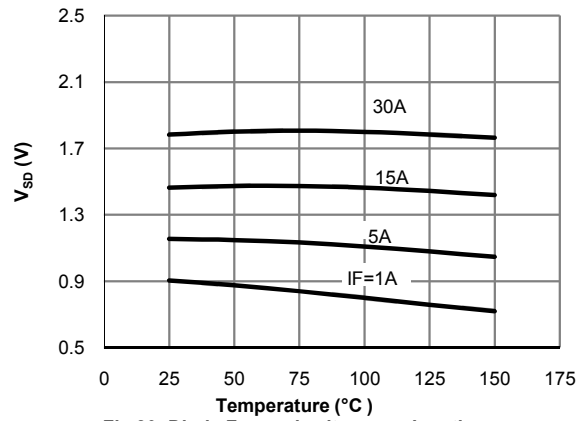


Fig 20: Diode Forward Voltage vs. Junction Temperature

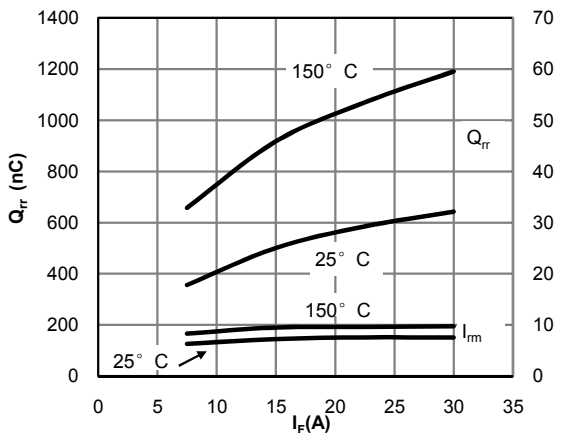


Fig 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

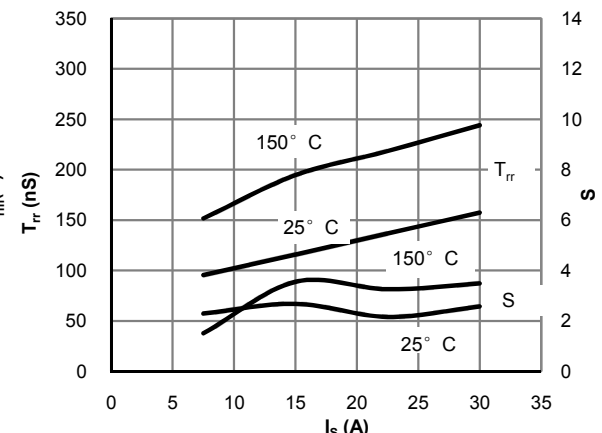


Fig 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

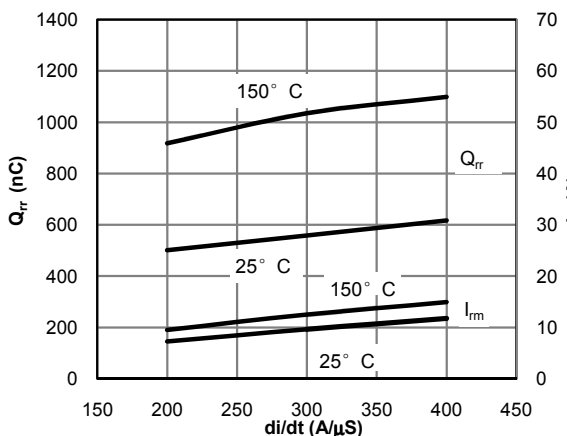


Fig 23: Diode Reverse Recovery Charge and Peak Current vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=15A$)

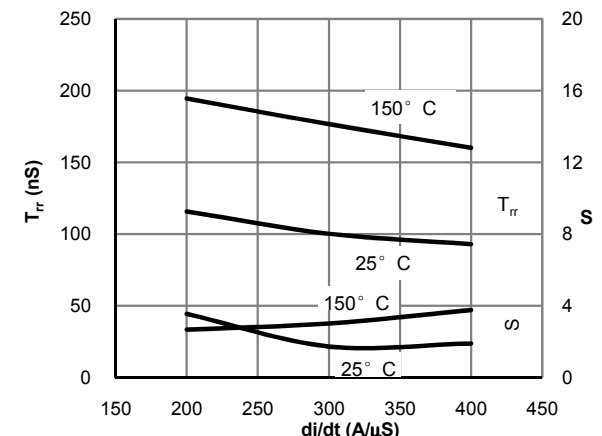


Fig 24: Diode Reverse Recovery Time and Softness Factor vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=15A$)

